

PARALLEL SPIRAL STACKED INDUCTOR ON SEMICONDUCTOR MATERIAL

ABSTRACT

A parallel spiral stacked inductor and manufacturing method therefore is provided. A substrate has a plurality of turns in a plurality of levels, the plurality of turns having a center proximate and a center distal ends. A first plurality of vias connecting the center proximate ends of the plurality of turns and a second plurality of vias connecting the center distal ends of the plurality of turns. A first connecting portion connects to the center proximate ends of the plurality of turns and a second connecting portion connecting to the center distal end of the plurality of turns. A dielectric material contains the inductor.

FIGURE 4



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